

FDS9431A_F085

P-Channel 2.5V Specified MOSFET

General Description

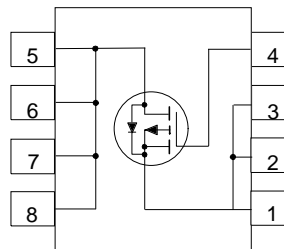
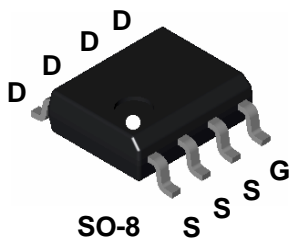
This P-Channel 2.5V specified MOSFET is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

Applications

- DC/DC converter
- Power management
- Load switch
- Battery protection

Features

- -3.5 A, -20 V. $R_{DS(ON)} = 0.130 \Omega @ V_{GS} = -4.5 V$
 $R_{DS(ON)} = 0.180 \Omega @ V_{GS} = -2.5 V$.
- Fast switching speed.
- High density cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Qualified to AEC Q101
- RoHS Compliant



Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 8	V
I_D	Drain Current - Continuous (Note 1a)	-3.5	A
	- Pulsed	-18	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1.0	
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

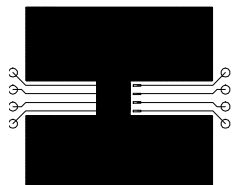
Device Marking	Device	Reel Size	Tape width	Quantity
FDS9431A	FDS9431A_F085	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

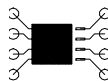
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		-28		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -16 V, V _{GS} = 0 V			-1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
On Characteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-0.6	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		2		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -4.5 V, I _D = -3.5 A V _{GS} = -2.5 V, I _D = -3.0 A V _{GS} = -4.5 V, I _D = -3.5 A T _J =125°C		0.110 0.140 0.155	0.130 0.180 0.220	Ω Ω Ω
I _{D(on)}	On-State Drain Current	V _{GS} = -4.5 V, V _{DS} = -5 V	-10			A
g _{FS}	Forward Transconductance	V _{DS} = -5 V, I _D = -3.5 A		6.5		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V, f = 1.0 MHz		405		pF
C _{oss}	Output Capacitance			170		pF
C _{rss}	Reverse Transfer Capacitance			45		pF
Switching Characteristics (Note 2)						
t _{d(on)}	Turn-On Delay Time	V _{DD} = -5 V, I _D = -1 A, V _{GS} = -4.5 V, R _{GEN} = 6 Ω		6.5	13	ns
t _r	Turn-On Rise Time			20	35	ns
t _{d(off)}	Turn-Off Delay Time			31	50	ns
t _f	Turn-Off Fall Time			21	35	ns
Q _g	Total Gate Charge	V _{DS} = -5 V, I _D = -3.5 A, V _{GS} = -4.5 V		6	8.5	nC
Q _{gs}	Gate-Source Charge			0.8		nC
Q _{gd}	Gate-Drain Charge			1.3		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current				-2.1	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.1 A (Note 2)		-0.7	-1.2	V

Notes:

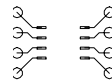
1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in^2 pad of 2 oz. copper.



b) 105°C/W when mounted on a 0.04 in^2 pad of 2 oz. copper.



c) 125°C/W on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

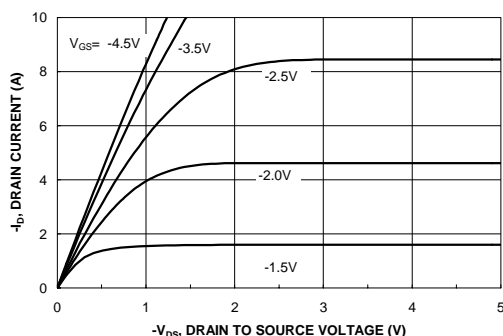


Figure 1. On-Region Characteristics.

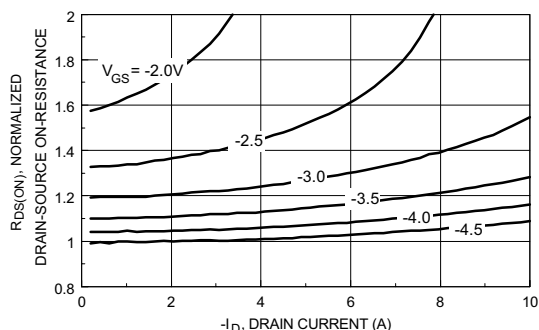


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

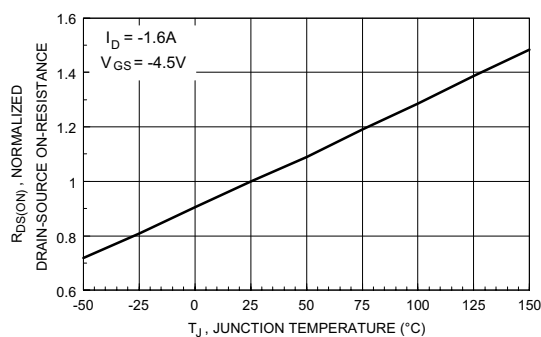


Figure 3. On-Resistance Variation with Temperature.

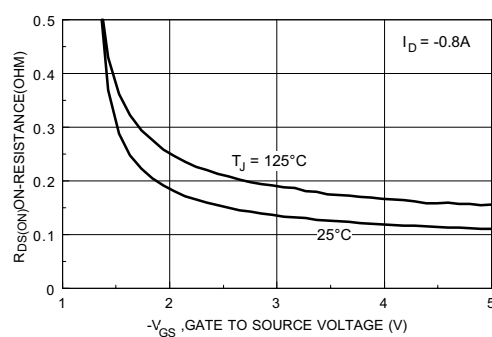


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

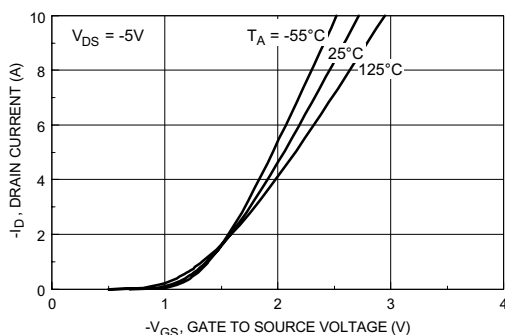


Figure 5. Transfer Characteristics.

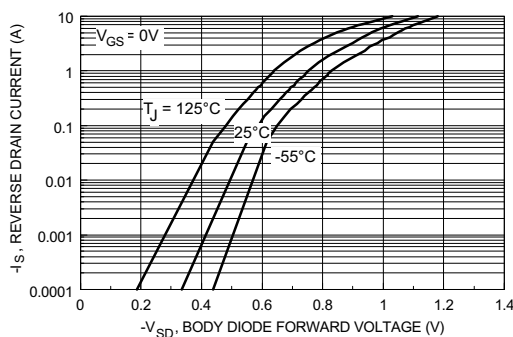


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

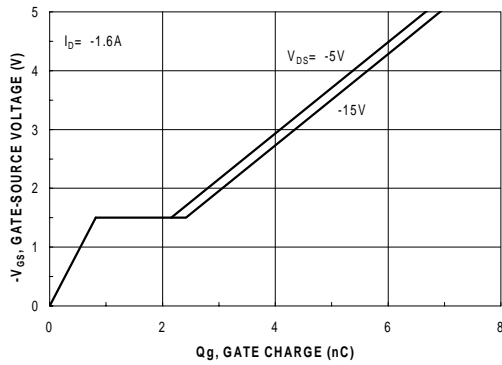


Figure 7. Gate Charge Characteristics.

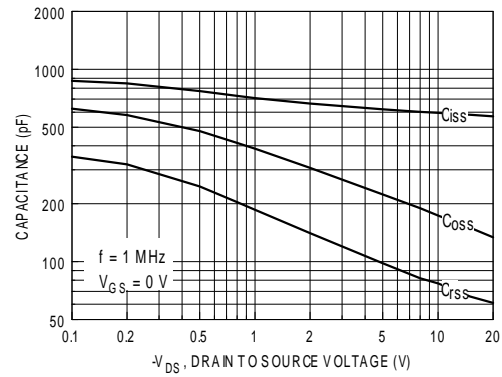


Figure 8. Capacitance Characteristics.

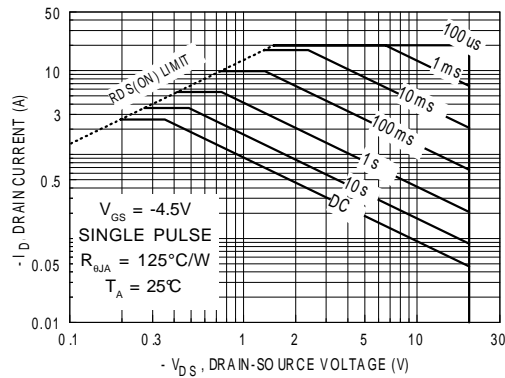


Figure 9. Maximum Safe Operating Area.

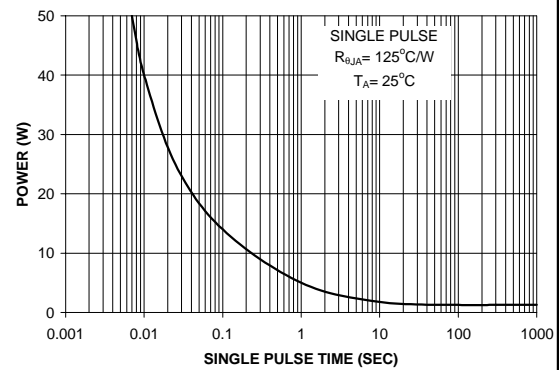


Figure 10. Single Pulse Maximum Power Dissipation.

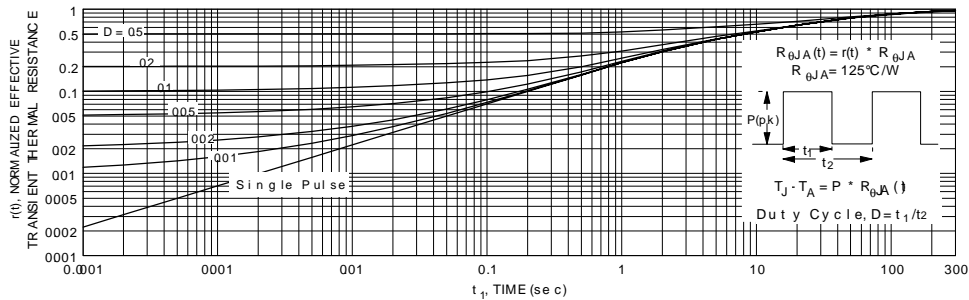


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.



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Rev. I47